

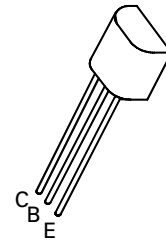
# PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

## ZTX550 ZTX551

ISSUE 1 – MARCH 94

### FEATURES

- \* 60 Volt  $V_{CEO}$
- \* 1 Amp continuous current
- \*  $P_{tot} = 1$  Watt



E-Line  
TO92 Compatible

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX550	ZTX551	UNIT
Collector-Base Voltage	$V_{CBO}$	-60	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-45	-60	V
Emitter-Base Voltage	$V_{EBO}$		-5	V
Peak Pulse Current	$I_{CM}$		-2	A
Continuous Collector Current	$I_C$		-1	A
Power Dissipation: at $T_{amb}=25^\circ\text{C}$ derate above $25^\circ\text{C}$	$P_{tot}$		1 5.7	W mW/°C
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200		°C

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ ).

PARAMETER	SYMBOL	ZTX550		ZTX551		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60		-80		V	$I_C = -100\mu\text{A}$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	-45		-60		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$		-0.1		-0.1	$\mu\text{A}$ $\mu\text{A}$	$V_{CB} = -45\text{V}$ $V_{CB} = -60\text{V}$
Emitter Cut-Off Current	$I_{EBO}$		-0.1		-0.1	$\mu\text{A}$	$V_{EB} = -4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.25		-0.35	V	$I_C = -150\text{mA}$ , $I_B = -15\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.1		-1.1	V	$I_C = -150\text{mA}$ , $I_B = -15\text{mA}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100 15	300	50 10	150		$I_C = -150\text{mA}$ , $V_{CE} = -10\text{V}^*$ $I_C = -1\text{A}$ , $V_{CE} = -10\text{V}^*$
Transition Frequency	$f_T$	150		150		MHz	$I_C = -50\text{mA}$ , $V_{CE} = -10\text{V}$ $f = 100\text{MHz}$

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## TYPICAL CHARACTERISTICS

